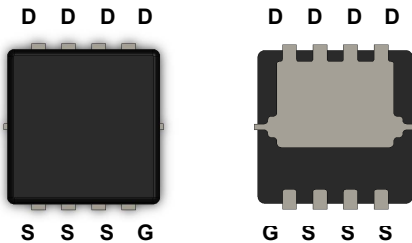


### General Description

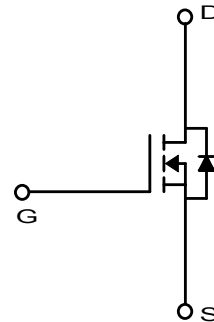
The MDV1525 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDV1525 is suitable for DC/DC converter and general purpose applications.

### Features

- $V_{DS} = 30V$
- $I_D = 24A @V_{GS} = 10V$
- $R_{DS(ON)} < 10.1m\Omega @V_{GS} = 10V$   
 $< 14.0m\Omega @V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested



PDFN33



### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$T_C=25^\circ C$ (Silicon limited)	$I_D$	37.2	A
	$T_C=25^\circ C$ (Package limited)		24	
	$T_C=70^\circ C$		24	
	$T_A=25^\circ C$		13.8 <sup>(3)</sup>	
	$T_A=70^\circ C$		11.1 <sup>(3)</sup>	
Pulsed Drain Current		$I_{DM}$	60	A
Power Dissipation	$T_C=25^\circ C$	$P_D$	24.5	W
	$T_C=70^\circ C$		15.6	
	$T_A=25^\circ C$		3.4 <sup>(3)</sup>	
	$T_A=70^\circ C$		2.2 <sup>(3)</sup>	
Single Pulse Avalanche Energy <sup>(2)</sup>		$E_{AS}$	48	mJ
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~150	°C

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	36	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	5.1	

## Ordering Information

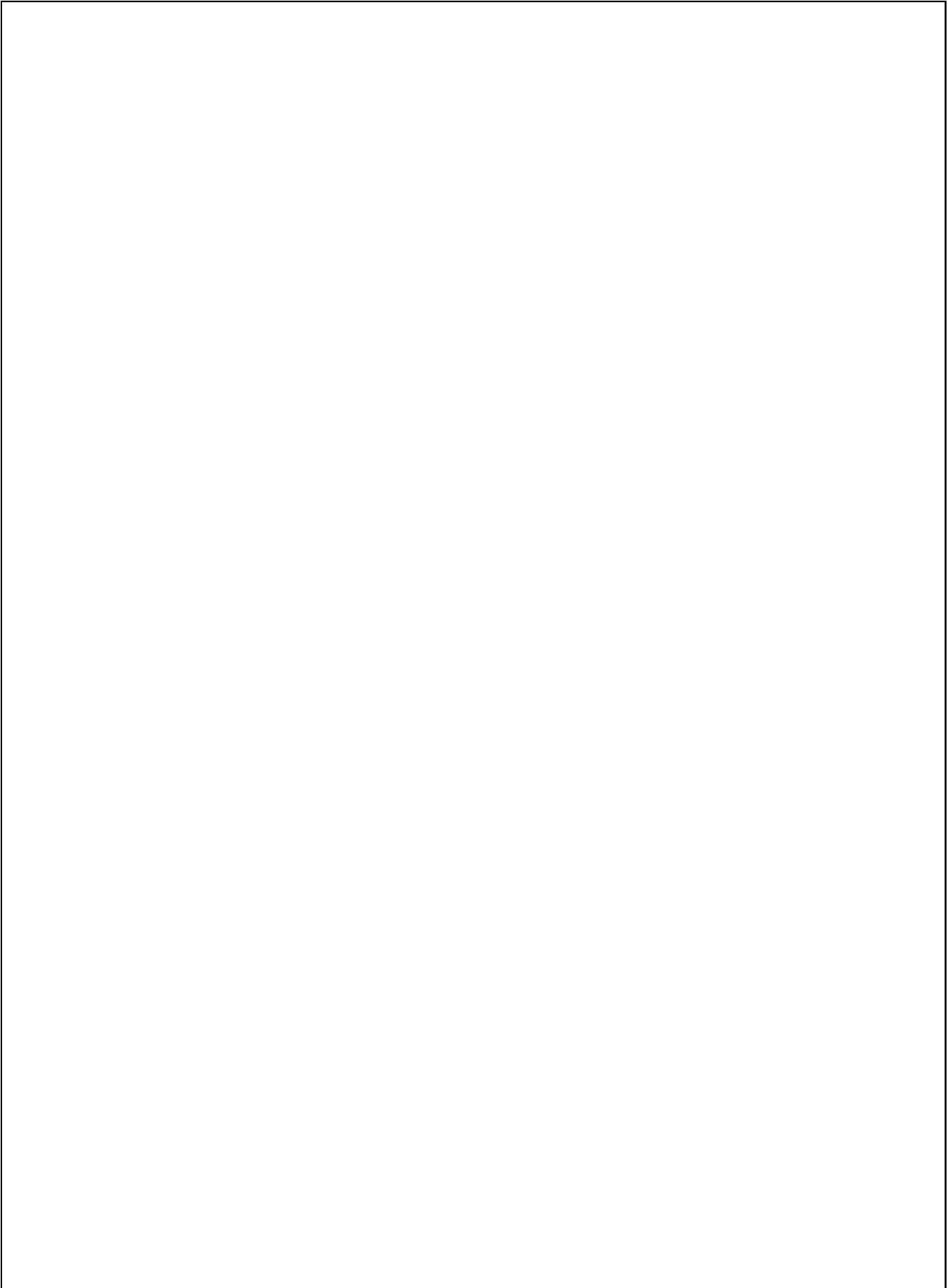
Part Number	Temp. Range	Package	Packing	Quantity	RoHS Status
MDV1525URH	-55~150°C	PowerDFN33	Tape & Reel	5000 units	Halogen Free

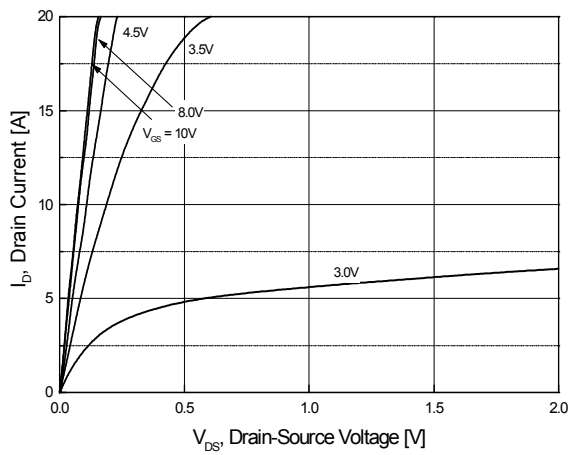
## Electrical Characteristics (T<sub>J</sub> = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.3	1.9	2.7	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V T <sub>J</sub> =55°C	-	-	1 5	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±0.1	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A T <sub>J</sub> =125°C	-	8.2 11.9	10.1 14.6	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9A	-	11.5	14.0	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 11A	-	27.3	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g(10V)</sub>	V <sub>DS</sub> = 15.0V, I <sub>D</sub> = 11A, V <sub>GS</sub> = 10V	8.8	12.6	16.4	nC
Total Gate Charge	Q <sub>g(4.5V)</sub>		4.2	6.0	7.8	
Gate-Source Charge	Q <sub>gs</sub>		-	2.5	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.8	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15.0V, V <sub>GS</sub> = 0V, f = 1.0MHz	568	811	1054	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		54	77	100	
Output Capacitance	C <sub>oss</sub>		108	154	200	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15.0V, I <sub>D</sub> = 11A, R <sub>G</sub> = 3.0Ω	-	6.8	-	ns
Rise Time	t <sub>r</sub>		-	11.8	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	20.0	-	
Fall Time	t <sub>f</sub>		-	7.1	-	
Gate Resistance	R <sub>g</sub>	f=1 MHz	1.0	1.6	3.0	Ω
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 11A, V <sub>GS</sub> = 0V	-	0.83	1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 11A, di/dt = 100A/μs	-	22.2	33.3	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	13.8	20.7	nC

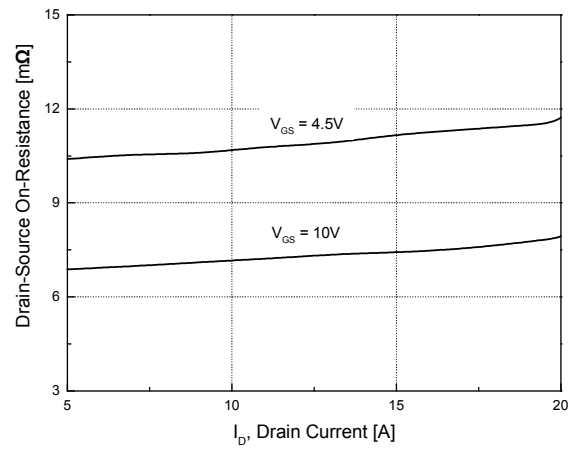
Note :

- Surface mounted FR-4 board by JEDEC (jesd51-7)
- E<sub>AS</sub> is tested at starting T<sub>J</sub> = 25°C, L = 0.1mH, I<sub>AS</sub> = 16.8A, V<sub>DD</sub> = 27V, V<sub>GS</sub> = 10V
- T < 10sec.

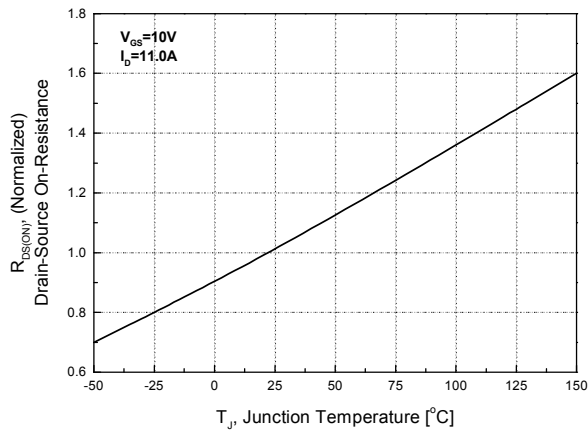




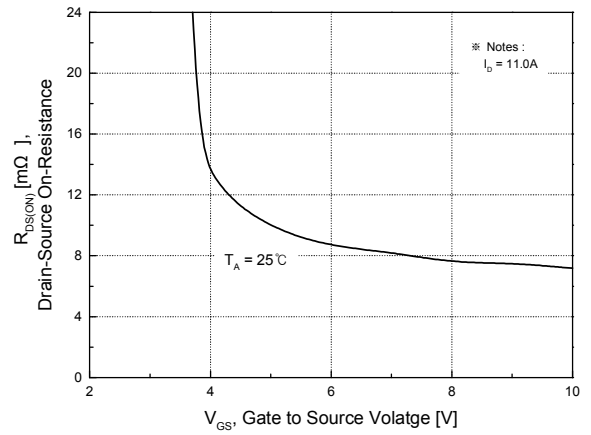
**Fig.1 On-Region Characteristics**



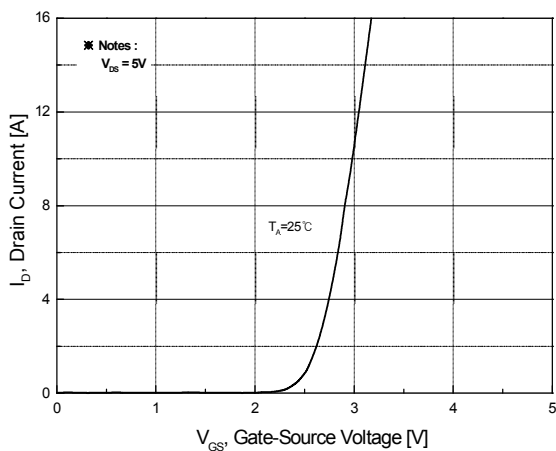
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



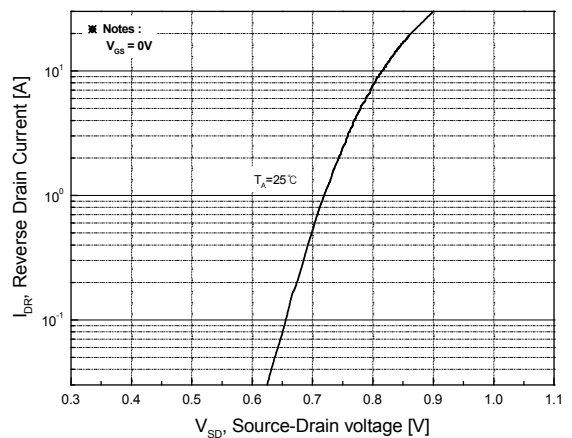
**Fig.3 On-Resistance Variation with Temperature**



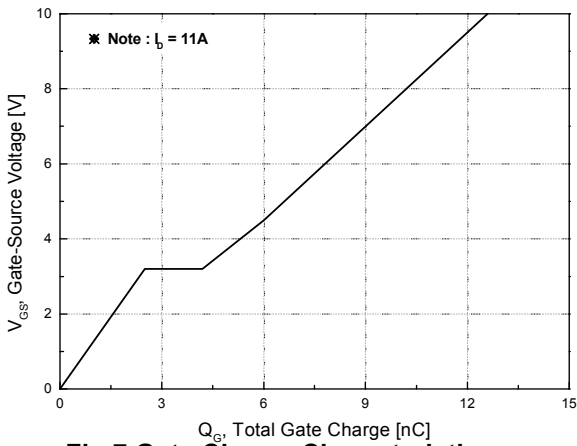
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



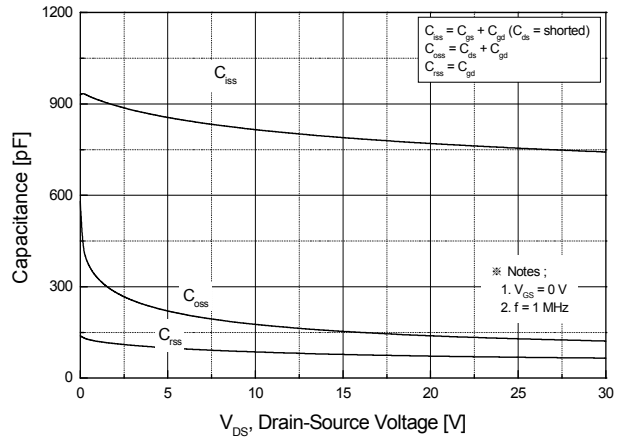
**Fig.5 Transfer Characteristics**



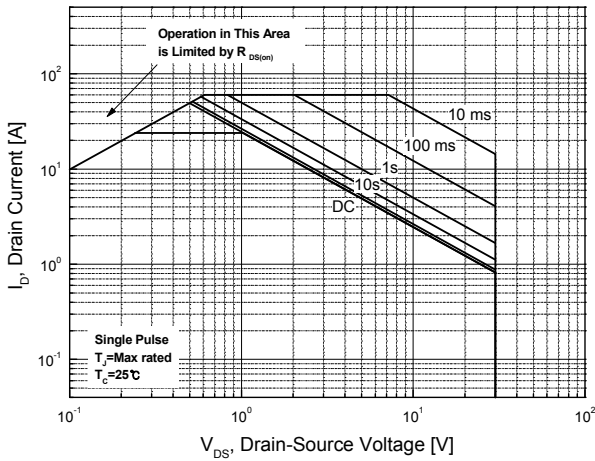
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



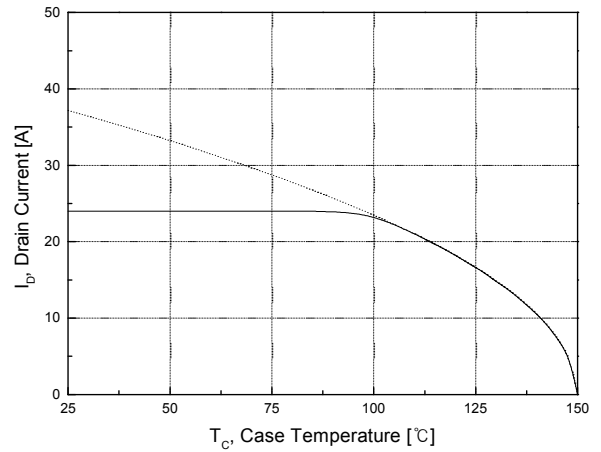
**Fig.7 Gate Charge Characteristics**



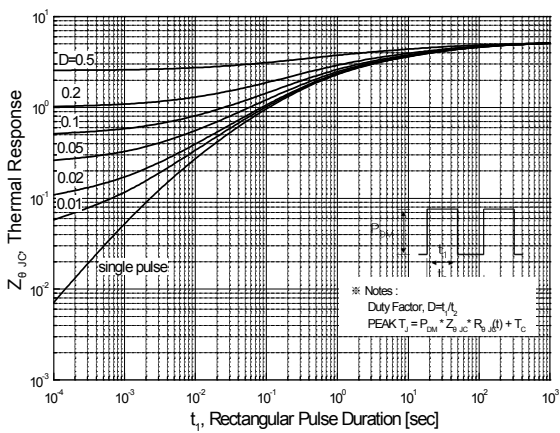
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**



**Fig.10 Maximum Drain Current vs. Case Temperature**

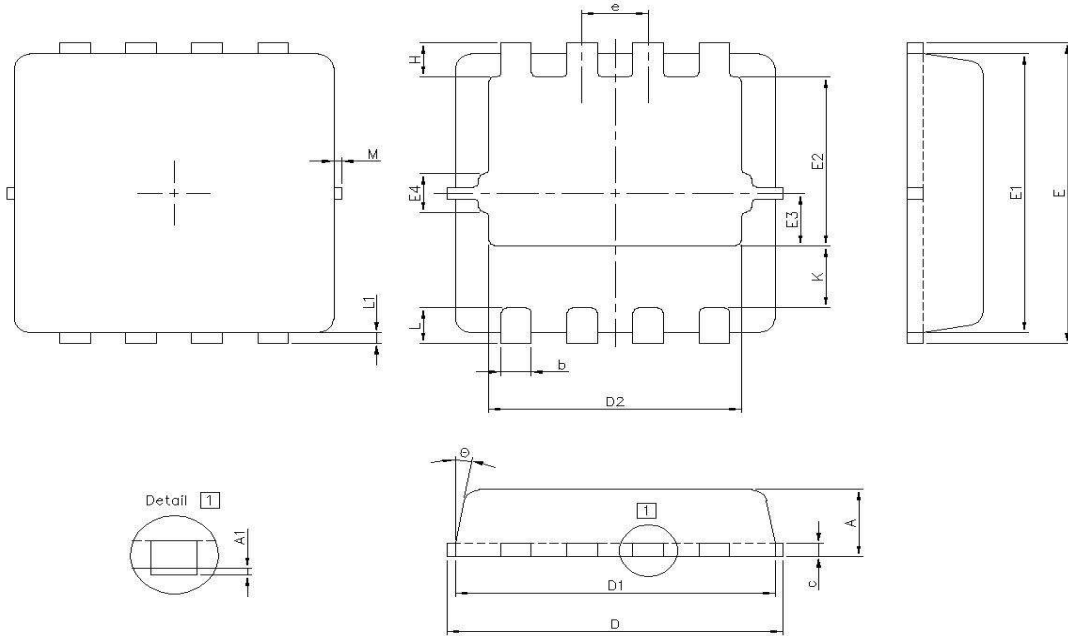


**Fig.11 Transient Thermal Response Curve**

## Package Dimension

### PowerDFN33 (3.3x3.3mm)

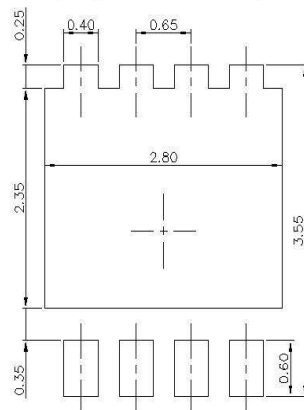
Dimensions are in millimeters, unless otherwise specified



(Unit: mm)


DIM	Min	Max	DIM	Min	Max
A	0.70	0.80	E2	1.78	1.98
A1	0.00	0.05	E3	0.49	0.69
b	0.25	0.35	E4	0.35 TYP.	
c	0.10	0.25	e	0.65 BSC	
D	3.20	3.40	K	0.70 TYP.	
D1	3.00	3.20	L	0.30	0.50
D2	2.39	2.59	L1	0.13 TYP.	
E	3.25	3.45	H	0.27	0.47
E1	3.00	3.20	Θ	0	12

Land Pattern  
(Only for Reference)



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